

ABSTRACT

The process of the present invention comprises reactive ion etching of  $Al_xF_yO_z$  oxide deposits on aluminum-containing bond pads using feed gases, such as,  $SF_6/CF_4/Ar$  or  $Cl_2/BCL_3/Ar$ , whose active plasma etches the  $Al_xF_yO_z$  oxide deposits by physical etching and chemical etching for more complete removal of the  $Al_xF_yO_z$  oxide deposits.